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0300 #7

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
STEVENSON

Serial No. 09/591,886

Filing Date: June 9, 2000

For: **IMPROVEMENTS IN OR RELATING
TO IMAGE SENSOR PACKAGING**



TRANSMITTAL OF CERTIFIED PRIORITY DOCUMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Transmitted herewith is a certified copy of the
priority United Kingdom Application No. 9923463.5.

Respectfully submitted,

A handwritten signature in cursive script, reading "John F. Woodson II".

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06OCT99 E481633-2 D02884
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1. Your reference

P23943A/EPE/JCO

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9923463.5

3. Full name, address and postcode of the or of each applicant (underline all surnames)

Vision Group plc
Aviation House
31 Pinkhill
Edinburgh
EH12 7BF

Patents ADP number (if you know it)

If the applicant is a corporate body, give the country/state of its incorporation

United Kingdom

7551773001

4. Title of the invention

"Improvements in or Relating to
Image Sensor Packaging"

5. Name of your agent (if you have one)

Murgitroyd & Company

"Address for service" in the United Kingdom to which all correspondence should be sent (including the postcode)

373 Scotland Street
GLASGOW
G5 8QA

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1198013

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9913516.2

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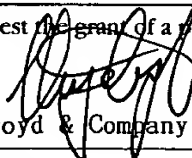
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1 "Improvements in or relating to Image Sensor Packaging"

2
3 The present invention relates to the packaging of
4 integrated circuits for use as image sensors ("image
5 sensor chips").

6
7 Most types of integrated circuits ("chips") require
8 "packaging" to encapsulate the sensitive chips and
9 provide mechanical protection during shipping, assembly
10 and subsequent use. Optical chips such as image
11 sensors are unusual in that it is necessary for their
12 packaging to include a transparent window to admit or
13 release light. In the case of image sensors, the
14 window allows light to impinge upon the optical sensor
15 array which forms part of the chip. The transparent
16 window, or lid, is commonly formed from glass.

17
18 Optical devices of this type are also unusually
19 difficult to manufacture because of stringent
20 requirements for cleanliness. Any foreign material
21 impinging on onto the surface of the sensor array can
22 cause image degradation leading to rejection of the
23 device and hence to higher component cost due to
24 reduced manufacturing yield.

25
26 Conventionally, image sensor packages are formed by
27 mounting a plurality of sensor chips in a rectangular
28 array on a substrate tile (typically of ceramic
29 material). After wire bonding, a lattice of "dam"
30 walls is written in liquid epoxy between the adjacent
31 chips, so that each chip is surrounded on all four

1 sides by a wall of epoxy material. A glass sheet is
2 then placed on the top surface, adhering to the tops of
3 the dam walls and encapsulating each chip in isolation
4 from the surrounding chips. The whole assembly is then
5 baked to harden the epoxy walls and then cut along the
6 lines of the walls between adjacent sensors to produce
7 a plurality of individual, encapsulated sensor devices.
8

9 This technique is very cost effective, but has a
10 significant disadvantage. Resin can bleed out of the
11 dam wall material when in the liquid state, running by
12 capillary action onto the chip surface and, in some
13 instances, onto the critical image sensing array area,
14 causing unacceptable image blemishes. Accordingly, the
15 manufacturing yield is reduced and the unit cost of the
16 sensor devices is increased.
17

18 This problem applies to both monochrome and colour
19 sensors, the latter having a thin layer (typically less
20 than 2 microns) of colour filter material (the
21 "mosaic") covering the sensitive array area.
22

23 It is an object of the present invention to provide
24 improved methods for packaging image sensors, and
25 improved image sensors formed thereby, in which the
26 above mentioned problem is obviated or mitigated.
27

28 In accordance with a first aspect of the present
29 invention, there is provided a method of manufacturing
30 an image sensor device of the type comprising an image
31 sensor chip, including an image sensor array formed on
32 a top surface thereof, mounted on a substrate and
33 encapsulated by means of a dam wall formed on the
34 substrate and surrounding the periphery of the sensor
35 chip and having a transparent lid member affixed to the
36 upper edges of said dam wall, wherein the method

1 includes forming a barrier on the surface of said
2 sensor chip and extending along at least a substantial
3 part of at least one side of said sensor array between
4 the sensor array and the dam wall.

5
6 Preferably, said barrier is formed with a height of at
7 least three microns.

8
9 Preferably, said barrier surrounds said sensor array.

10
11 Preferably, said barrier is formed during fabrication
12 of the sensor chip.

13
14 Preferably, where said sensor chip is a colour image
15 sensor including a mosaic of colour filter material
16 overlying said sensor array, said barrier is formed
17 from said colour filter material simultaneously with
18 the formation of said mosaic. Most preferably, said
19 barrier is formed from a plurality of layers
20 corresponding to a plurality of colours of filter
21 material forming said mosaic.

22
23 In accordance with a second aspect of the invention,
24 there is provided an image sensor chip, including an
25 image sensor array formed on a top surface thereof,
26 including a barrier formed on the surface of said
27 sensor chip and extending along at least a substantial
28 part of at least one side of said sensor array.

29
30 Preferably, said barrier is formed with a height of at
31 least three microns.

32
33 Preferably, said barrier surrounds said sensor array.

34
35 Preferably, where said sensor chip is a colour image
36 sensor including a mosaic of colour filter material

1 overlying said sensor array, said barrier is formed
2 from said colour filter material simultaneously with
3 the formation of said mosaic. Most preferably, said
4 barrier is formed from a plurality of layers
5 corresponding to a plurality of colours of filter
6 material forming said mosaic.

7
8 In accordance with a third aspect of the present
9 invention, there is provided an image sensor device of
10 the type comprising an image sensor chip, including an
11 image sensor array formed on a top surface thereof,
12 mounted on a substrate and encapsulated by means of a
13 dam wall formed on the substrate and surrounding the
14 periphery of the sensor chip and having a transparent
15 lid member affixed to the upper edges of said dam wall,
16 wherein the sensor chip includes a barrier formed on
17 the surface thereof and extending along at least a
18 substantial part of at least one side of said sensor
19 array between the sensor array and the dam wall.

20
21 Preferably, said barrier is formed with a height of at
22 least three microns.

23
24 Preferably, said barrier surrounds said sensor array.

25
26 Preferably, where said sensor chip is a colour image
27 sensor including a mosaic of colour filter material
28 overlying said sensor array, said barrier is formed
29 from said colour filter material simultaneously with
30 the formation of said mosaic. Most preferably, said
31 barrier is formed from a plurality of layers
32 corresponding to a plurality of colours of filter
33 material forming said mosaic.

34
35 Embodiments of the invention will now be described, by
36 way of example only, with reference to the accompanying

1 drawings, in which:

2

3 Fig. 1 is a plan view of a substrate having a plurality
4 of image sensor chips mounted thereon; and

5

6 Fig. 2 is a sectional side view of an embodiment of an
7 image sensor device formed in accordance with the
8 present invention.

9

10 Referring now to the drawings, Fig. 1 shows a substrate
11 10, typically of ceramic material, having an array of
12 individual image sensor chips 12 mounted on an upper
13 surface thereof. Each of the chips 12 includes an
14 image sensor array (not shown) on its top surface.

15

16 In accordance with a conventional manufacturing
17 process, after wire bonding, the individual chips 12
18 are encapsulated in situ on the substrate by writing
19 dam walls (14, Fig. 2) of liquid epoxy material along
20 the gaps between the chips 12 and around the periphery
21 of the array of chips 12. As seen in Fig. 2, the dam
22 walls 14 are formed on the surface of the substrate 10
23 and overlap the edges of the chips 12. A glass sheet
24 (16, Fig. 2) is then laid on top of the dam walls 14
25 and bonded to their upper edges, so that each chip 12
26 is encapsulated between the substrate 10, dam walls 14
27 and glass sheet 16. The whole assembly is then baked
28 to harden the dam walls 14 and diced by sawing along
29 the dam walls 14 between the chips 12 and around the
30 periphery of the array of chips 12 to produce a
31 plurality of individual, packaged devices.

32

33 Fig. 2 shows a cross sectional view of a single image
34 sensor device formed in this manner.

35

36 As noted above, a problem which arises with this

1 manufacturing technique is that resin can bleed out of
2 the dam walls 14 while in the liquid state, running by
3 capillary action over the chip surface and thereby onto
4 the image sensing area, causing unacceptable image
5 blemishes. Such resin bleed is indicated at 18 in Fig.
6 2.

7
8 In accordance with the present invention, this problem
9 is obviated or mitigated by forming a barrier 20 on the
10 chip surface between the dam walls 14 and the image
11 sensing array of the chip 12. Such a barrier 20
12 impedes the progress of the liquid resin and prevents
13 it impinging onto the sensor array 22. It has been
14 found that a barrier at least about 3 microns in height
15 is effective in arresting the resin bleed 18. The
16 barrier 20 may extend around the entire periphery of
17 the sensor array 22. However, depending on the size
18 and location of the sensor array 22 on the chip surface
19 in relation to the dam walls 14, it may be sufficient
20 to form the barrier 20 along at least a substantial
21 part of at least one edge of the sensor array 22.

22
23 The barrier 20 may be formed during fabrication of the
24 image sensor chips 12 as an integral part of the
25 manufacturing process, being deposited by means of any
26 conventional chip fabrication process such as
27 photolithography. The barrier 20 may be formed from
28 materials which are conventionally used in the
29 fabrication of the image sensor circuitry on a
30 semiconductor wafer, so that the invention may be
31 implemented at, effectively, zero cost.

32
33 In the case of a colour image sensor, it is
34 particularly preferred that the barrier be built from
35 the materials used to form the conventional three-
36 colour filter mosaic on top of the image sensing

1 circuit. The colour filter material is typically of
2 the order of one micron in thickness, so that stacking
3 all three colours of material on top of one another in
4 the barrier area provides the required barrier height
5 of about three microns, without adding to existing
6 manufacturing costs. This barrier construction is
7 illustrated in detail 24 of Fig. 2.

8
9 The invention thus provides improved image sensor
10 chips, packaged image sensor devices and methods of
11 manufacturing the same.

12
13 Modifications and improvements may be incorporated
14 without departing from the scope of the invention.
15

1 Claims

2
3 1. A method of manufacturing an image sensor device
4 of the type comprising an image sensor chip, including
5 an image sensor array formed on a top surface thereof,
6 mounted on a substrate and encapsulated by means of a
7 dam wall formed on the substrate and surrounding the
8 periphery of the sensor chip and having a transparent
9 lid member affixed to the upper edges of said dam wall,
10 wherein the method includes forming a barrier on the
11 surface of said sensor chip and extending along at
12 least a substantial part of at least one side of said
13 sensor array between the sensor array and the dam wall.

14
15 2. A method as claimed in Claim 1, wherein said
16 barrier is formed with a height of at least three
17 microns.

18
19 3. A method as claimed in Claim 1 or Claim 2, wherein
20 said barrier surrounds said sensor array.

21
22 4. A method as claimed in any preceding Claim,
23 wherein said barrier is formed during fabrication of
24 the sensor chip.

25
26 5. A method as claimed in any preceding Claim,
27 wherein said sensor chip is a colour image sensor
28 including a mosaic of colour filter material overlying
29 said sensor array, and said barrier is formed from said
30 colour filter material simultaneously with the
31 formation of said mosaic.

32
33 6. A method as claimed in Claim 5, wherein said
34 barrier is formed from a plurality of layers
35 corresponding to a plurality of colours of filter
36 material forming said mosaic.

1 7. An image sensor chip, including an image sensor
2 array formed on a top surface thereof, further
3 including a barrier formed on the surface of said
4 sensor chip and extending along at least a substantial
5 part of at least one side of said sensor array.

6
7 8. An image sensor chip as claimed in Claim 7,
8 wherein said barrier is formed with a height of at
9 least three microns.

10
11 9. An image sensor chip as claimed in Claim 7 or
12 Claim 8, wherein said barrier surrounds said sensor
13 array.

14
15 10. An image sensor chip as claimed in any one of
16 Claims 7 to 9, wherein said sensor chip is a colour
17 image sensor including a mosaic of colour filter
18 material overlying said sensor array, and said barrier
19 is formed from said colour filter material
20 simultaneously with the formation of said mosaic.

21
22 11. An image sensor chip as claimed in Claim 10,
23 wherein said barrier is formed from a plurality of
24 layers corresponding to a plurality of colours of
25 filter material forming said mosaic.

26
27 12. An image sensor device of the type comprising an
28 image sensor chip, including an image sensor array
29 formed on a top surface thereof, mounted on a substrate
30 and encapsulated by means of a dam wall formed on the
31 substrate and surrounding the periphery of the sensor
32 chip and having a transparent lid member affixed to the
33 upper edges of said dam wall, wherein the sensor chip
34 includes a barrier formed on the surface thereof and
35 extending along at least a substantial part of at least
36 one side of said sensor array between the sensor array

1 and the dam wall.

2

3 13. An image sensor device as claimed in Claim 12,
4 wherein said barrier is formed with a height of at
5 least three microns.

6

7 14. An image sensor device as claimed in Claim 12 or
8 Claim 13, wherein said barrier surrounds said sensor
9 array.

10

11 15. An image sensor device as claimed in any one of
12 Claims 12 to 14, wherein said sensor chip is a colour
13 image sensor including a mosaic of colour filter
14 material overlying said sensor array, and said barrier
15 is formed from said colour filter material
16 simultaneously with the formation of said mosaic.

17

18 16. An image sensor device as claimed in Claim 15,
19 wherein said barrier is formed from a plurality of
20 layers corresponding to a plurality of colours of
21 filter material forming said mosaic.

22

1 Abstract (Fig. 2)

2
3 An image sensor device comprises an image sensor chip
4 (12), including an image sensor array (22) formed on a
5 top surface thereof, mounted on a substrate (10) and
6 encapsulated by means of a dam wall (14) formed on the
7 substrate and surrounding the periphery of the sensor
8 chip and having a transparent lid member (16) affixed
9 to the upper edges of the dam wall. A barrier (20) is
10 formed on the surface of the chip, extending along at
11 least a substantial part of at least one side of the
12 sensor array between the sensor array and the dam wall.
13 Preferably, the barrier is formed with a height of at
14 least three microns and surrounds the sensor array.
15 The barrier may be formed during fabrication of the
16 sensor chip. Where the sensor chip is a colour image
17 sensor including a mosaic of colour filter material
18 overlying said sensor array, the barrier may be formed
19 from the colour filter material simultaneously with the
20 formation of the mosaic. The barrier prevents resin
21 bleeding from the dam wall onto the surface of the
22 sensor array.

1/2

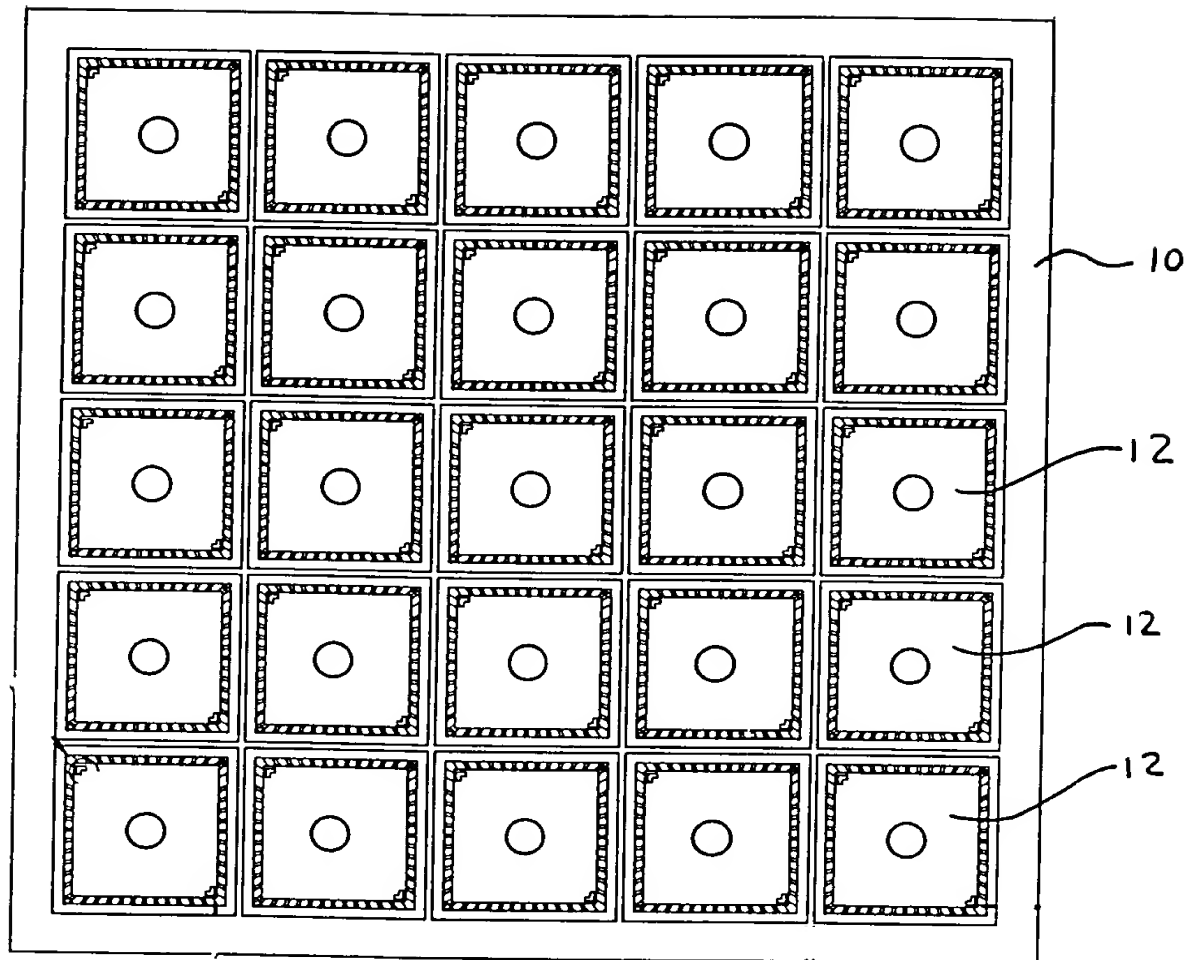


FIG. 1

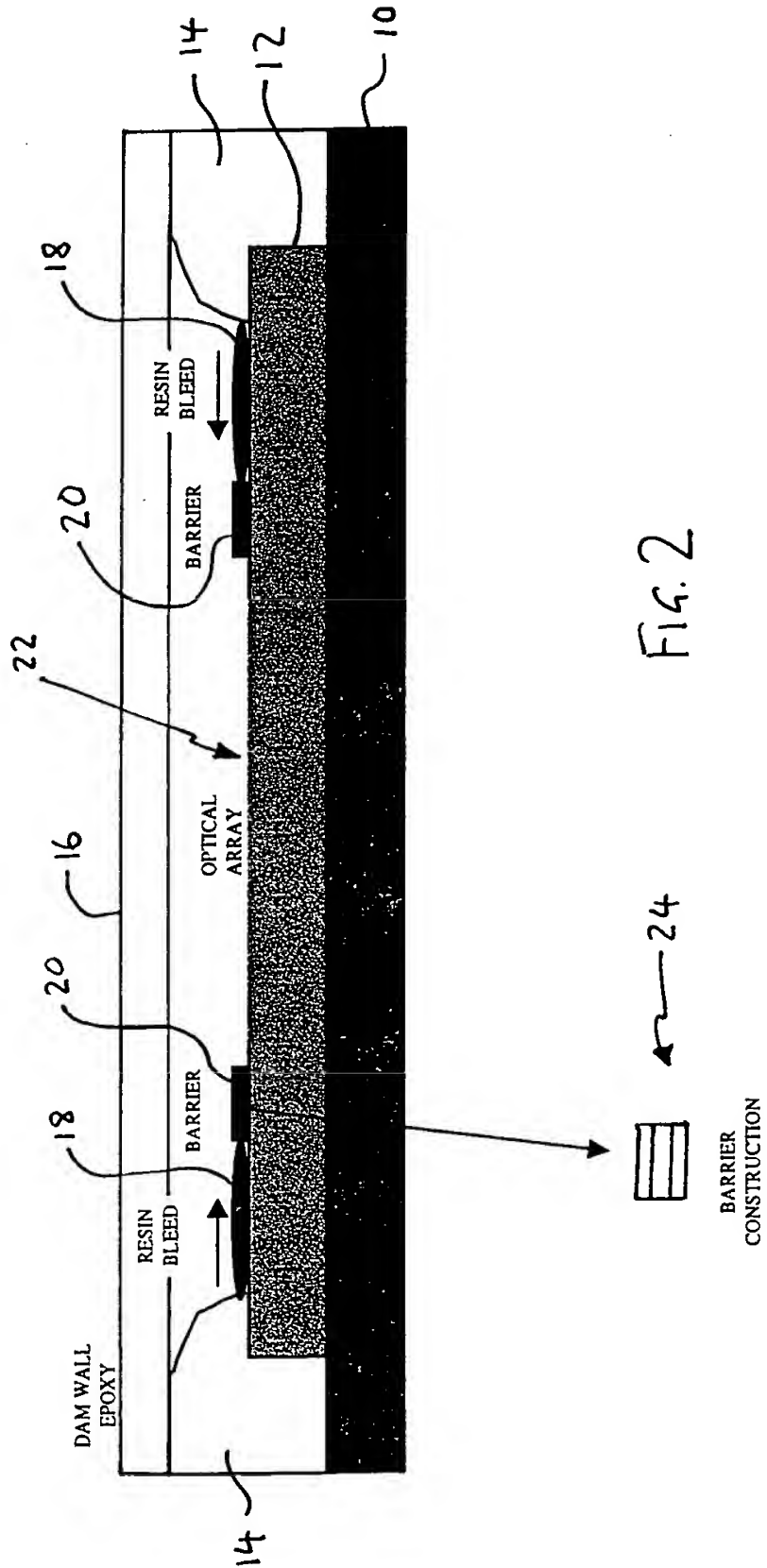


FIG. 2